

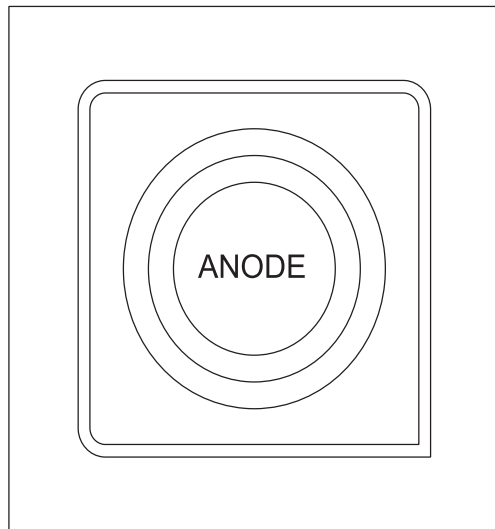
PROCESS CPD92X
Schottky Diode
High Voltage Schottky Diode Chip



PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	9.0 x 9.0 MILS
Die Thickness	5.9 MILS
Anode Bonding Pad Area	4.8 MILS DIAMETER
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 12,000Å

GEOMETRY



BACKSIDE CATHODE

R0

GROSS DIE PER 5 INCH WAFER

209,532

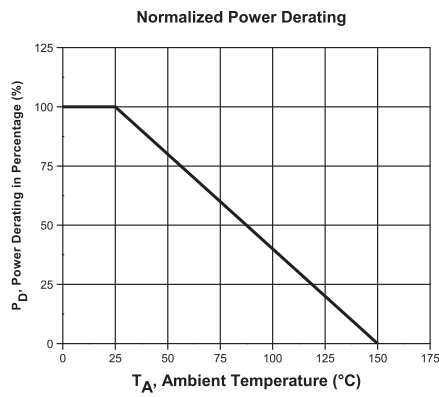
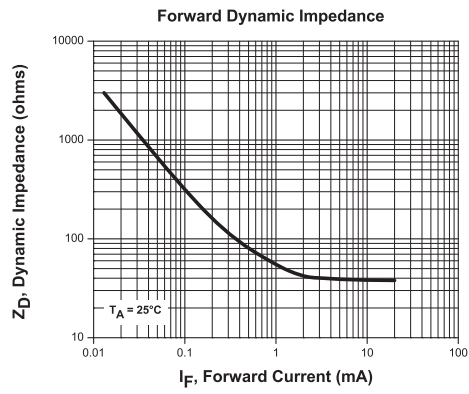
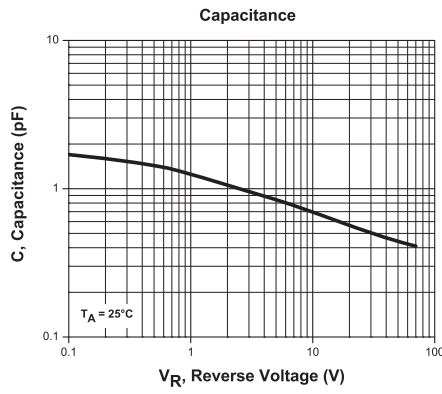
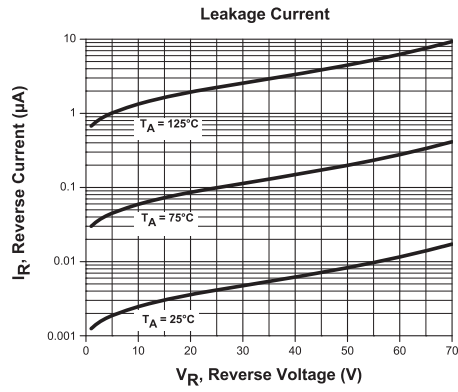
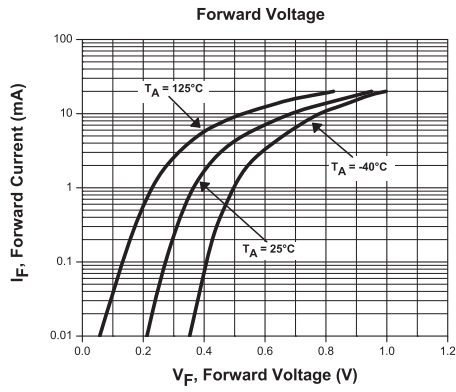
PRINCIPAL DEVICE TYPES

CMDD6263
CMKD6263
CMLD6263 Series
CMOD6263
CMPD6263 SERIES
CMSD6263 SERIES
CMUD6263 Series
1N6263

R1 (22-March 2010)

PROCESS CPD92X

Typical Electrical Characteristics



R1 (22-March 2010)